Phantom III Inductively Coupled Plasma/Reactive Ion Etching

Plasma initiated by applying a strong radio frequency electromagnetic field to the wafer platter is used to etch a variety of materials, including but not limited to II-VI and III-V compound semiconductors, dielectrics, quartz, glass, silicon, silicon compounds, and metals.

Specifications

- Six processing gases of BCl_3, SF_6, O_2, Cl_2, CHF_3, CF4
- AlGaAs, Au, Carbon, Cr, Cu, GaN, InAlGaN, InGaAs, InGaN, GaN, InP, Pt, Si, SiC, Ti, Pr, and organic material
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